

P-Channel MOSFET

2SJ287

■ Features

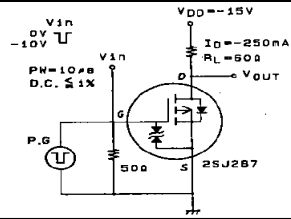
- $V_{DS}(V) \approx -30V$
- $I_D \approx -500mA$
- $R_{DS(ON)} < 2.2\Omega$ ($V_{GS} = -10V$)
- $R_{DS(ON)} < 3.3\Omega$ ($V_{GS} = -4V$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 15	
Continuous Drain Current	I_D	-0.5	A
Pulsed Drain Current (Note.1)	I_{DM}	-2	
Power Dissipation $T_c = 25^\circ C$	P_D	3.5	W
		1.3	
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

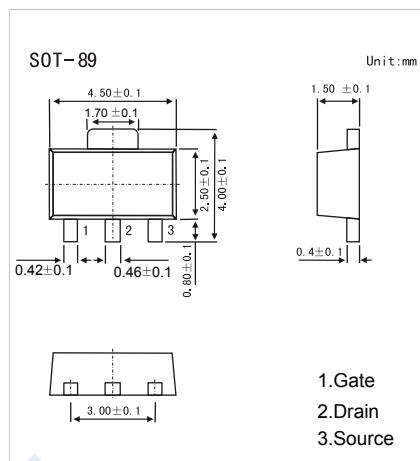
Note.1: $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -1mA, V_{GS} = 0V$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-100	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 10	μA
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -250mA$			2.2	Ω
		$V_{GS} = -4V, I_D = -250mA$			3.3	
Forward Transconductance	g_{FS}	$V_{DS} = -10V, I_D = -250mA$	240	400		mS
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$		50		pF
Output Capacitance	C_{oss}			35		
Reverse Transfer Capacitance	C_{rss}			10		
Turn-On DelayTime	$t_{d(on)}$			7		ns
Turn-On Rise Time	t_r			10		
Turn-Off DelayTime	$t_{d(off)}$			35		
Turn-Off Fall Time	t_f			20		
Diode Forward Voltage	V_{SD}	$I_S = -0.5A, V_{GS} = 0V$		-1		V

■ Marking

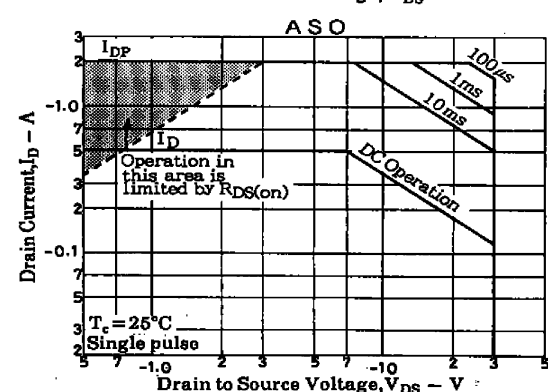
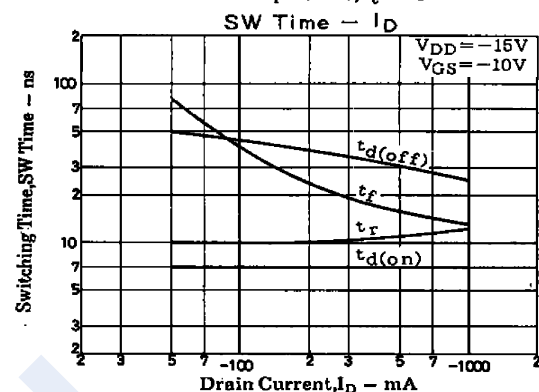
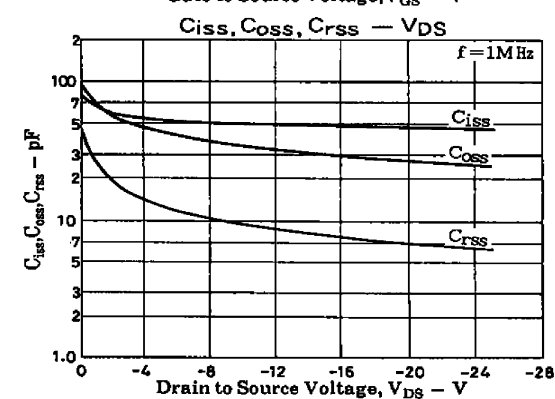
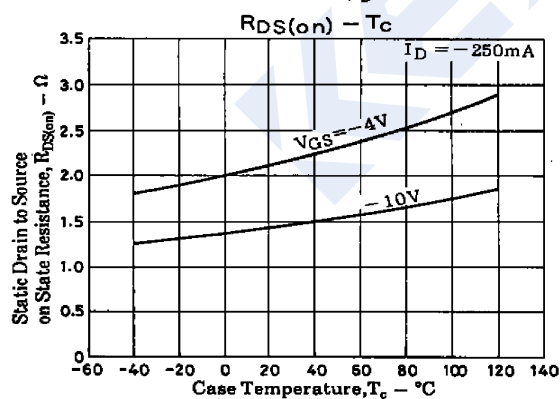
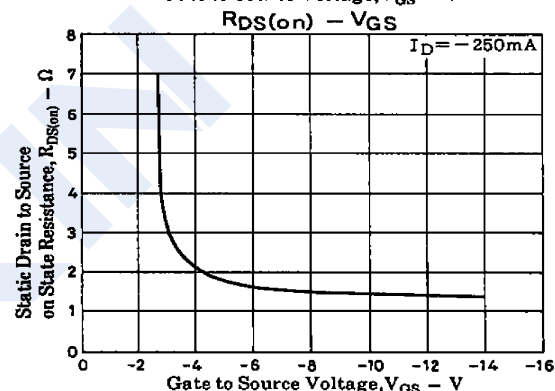
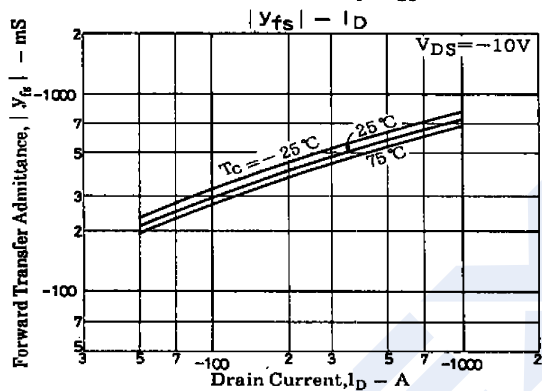
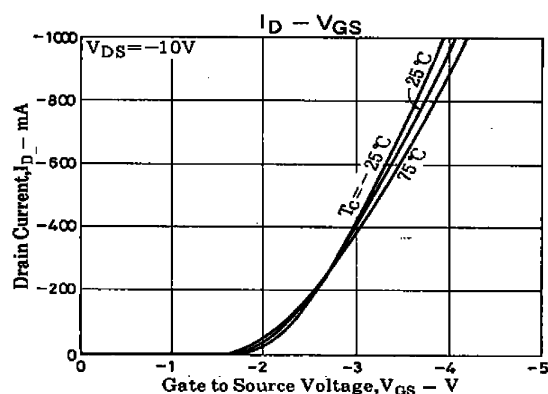
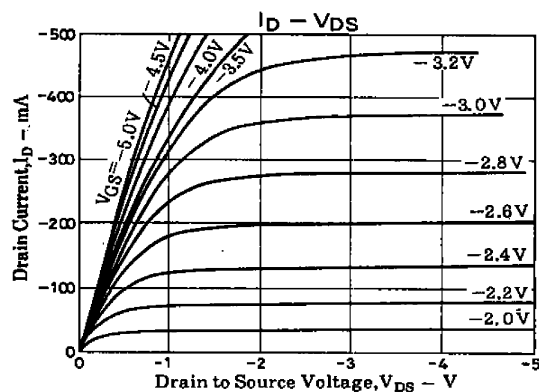
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■ Typical Characteristics



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